



DMN3025LFV

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	18mΩ @ V _{GS} = 10V	25A
30V	30mΩ @ V _{GS} = 4.5V	20A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

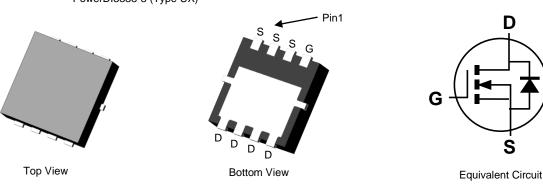
30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UX)

Features and Benefits

- Low R_{DS(ON)} Ensures On State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3025LFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel
DMN3025LFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



<u>L25</u>= Product Type Marking Code <u>YY</u>WW = Date Code Marking <u>YY</u> = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

PowerDI3333-8 (Type UX)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	30	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 7) $V_{GS} = 10V$	T _C = +25°C T _C = +70°C	ID	25 20	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	55	А	
Maximum Continuous Body Diode Forward Current (Note 6)	ls	3	А	
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	14	А	
Avalanche Energy, L = 0.1mH (Note 8)	E _{AS}	9.8	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	146	°C/W
Total Power Dissipation (Note 6)		PD	2.2	W
nal Resistance, Junction to Ambient (Note 6) Steady State		$R_{\theta JA}$	57	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _θ JC	4.5	0/00
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	-	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Deserve	-	13	18	mΩ	$V_{GS} = 10V, I_D = 7A$	
	R _{DS(ON)}	-	21	30	mΩ	V _{GS} = 4.5V, I _D = 7A	
Diode Forward Voltage	V _{SD}	-	0.7	1.2	V	$V_{GS} = 0V, I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	-	500	-	pF		
Output Capacitance	Coss	-	72	-	pF	− V _{DS} = 15V, V _{GS} = 0V, − f = 1MHz	
Reverse Transfer Capacitance	Crss	-	57	-	pF		
Gate Resistance	Rg	-	1.9	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	4.6	-	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	-	9.8	-	nC	V 15V I 10A	
Gate-Source Charge	Q _{gs}	-	1.6	-	nC	$V_{DS} = 15V, I_D = 10A$	
Gate-Drain Charge	Q _{gd}	-	2.0	-	nC		
Turn-On Delay Time	t _{D(ON)}	-	3.9	-	ns	V _{DD} = 15V, V _{GS} = 10V,	
Turn-On Rise Time	t _R	-	4.2	-	ns		
Turn-Off Delay Time	t _{D(OFF)}	-	16.6	-	ns	$R_g = 6\Omega, I_D = 1A$	
Turn-Off Fall Time	t _F	-	5.8	-	ns	7	
Body Diode Reverse Recovery Time	t _{RR}	-	5.6	-	ns	- I _F = 12A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Q _{RR}	-	2.6	-	nC		

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad).

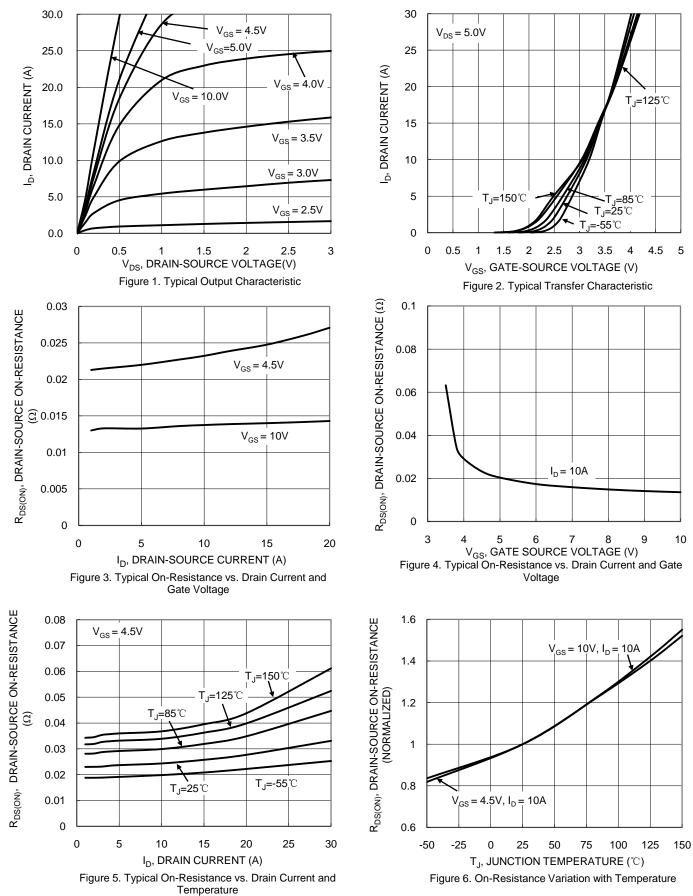
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.



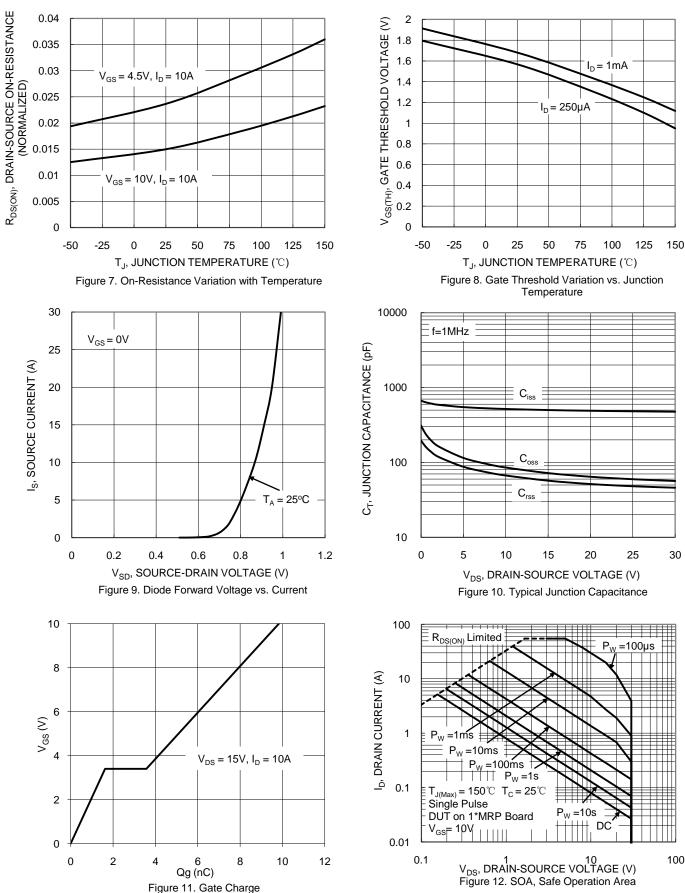
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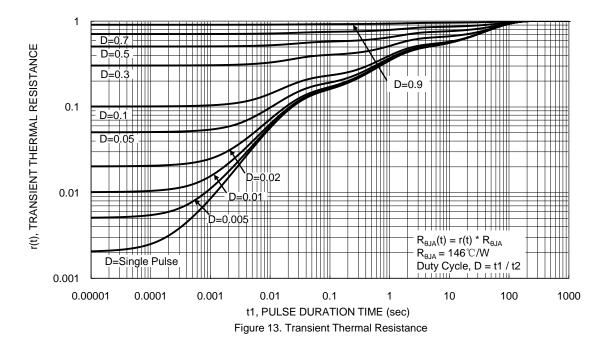
DMN3025LFV Document number: DS39950 Rev. 2 - 2



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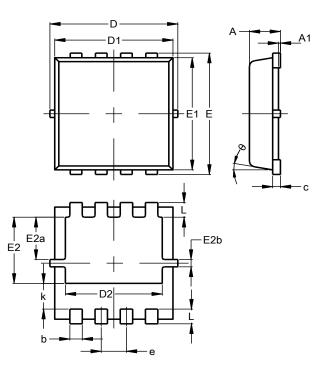






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



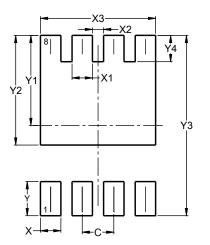
PowerDI3333-8 (Type UX)

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Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
c	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
ш	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
e	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)				
С	0.650				
Х	0.420				
X1	0.420				
X2	0.230				
X3	2.370				
Y	0.700				
Y1	1.850				
Y2	2.250				
Y3	3.700				
Y4	0.540				



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